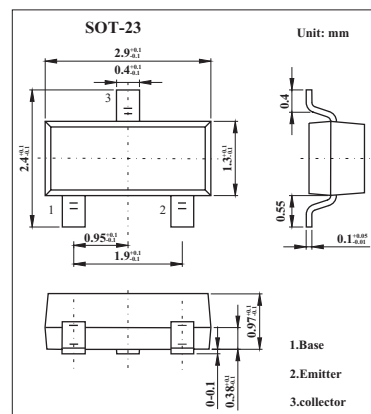


## PNP Epitaxial Planar Silicon Transistors

## 2SA1252

## ■ Features

- High  $V_{EBO}$ .
- Wide ASO and high durability against breakdown.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-60	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-15	V
Collector current	$I_C$	-150	mA
Collector current (pulse)	$I_{CP}$	-300	mA
Collector dissipation	$P_C$	200	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -10V, I_C = 0$			-0.1	$\mu\text{A}$
DC current Gain	$h_{FE}$	$V_{CE} = -6V, I_C = -1\text{mA}$	90		560	
Gain bandwidth product	$f_T$	$V_{CE} = -6V, I_C = -1\text{mA}$		100		MHz
Output capacitance	$C_{ob}$	$V_{CB} = -6V, f = 1\text{MHz}$		3.5		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.5	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, R_{BE} = \infty$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-15			V

■  $h_{FE}$  Classification

Marking	D4	D5	D6	D7
$h_{FE}$	90~180	135~270	200~400	300~600